**Amendments to the Claims:**

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of forming shallow trench isolation regions comprising ~~the steps of~~:

forming a plurality of active regions on a silicon substrate;

forming a shallow trench isolation region between a first and a second active region from among the plurality of active regions; and

selectively depositing silicon dioxide in the shallow trench isolation region without depositing the silicon dioxide on the first and second active regions.

2. (Currently amended) The method according to claim 1, wherein the ~~depositing step is performed~~ the silicon dioxide is deposited by liquid phase deposition of the silicon dioxide.

3. (Currently amended) The method according to claim 1, wherein the silicon substrate includes:

a silicon substrate;

a buried oxide layer on the silicon substrate; and

a silicon-on-insulator layer on the buried oxide layer and from which the active regions are formed.

4. (Withdrawn-currently amended) The method according to claim 3, further comprising ~~the step of~~:

forming a pad oxide layer on the silicon-on-insulator layer.

5. (Withdrawn-currently amended) The method according to claim 4, wherein the pad oxide layer has a thickness [[of]] between approximately 2 nm [[-]] and approximately 10 nm.

6. (Currently Amended) The method according to claim 3, further comprising:

~~the step of~~ forming a pad nitride layer.

7. (Currently Amended) The method according to claim 6, wherein the pad nitride layer has a thickness [[of]] between approximately 10 nm and [[-]] approximately 150 nm.

8. (Currently Amended) The method according to claim 1, further comprising ~~the step of~~:

cleaning the shallow trench isolation region before ~~performing the~~ selectively depositing [[step]] silicon dioxide.

9. (Currently Amended) The method according to claim 8, wherein ~~the step of~~ cleaning the shallow trench isolation region reduces an amount of native oxide present along each exposed wall of the shallow trench isolation region.

10. (Original) The method according to claim 6, wherein the shallow trench isolation region extends through the pad nitride layer and the silicon-on-insulator layer to reach the buried oxide layer.

11. (Currently Amended) The method according to claim 10, wherein [[the]] selective depositing [[of]] the silicon dioxide further includes ~~the step of~~:

depositing the silicon dioxide so that the silicon dioxide nucleates on and grows from the buried oxide layer.

12. (Currently Amended) The method according to claim 1, further comprising ~~the steps of~~:

overfilling the shallow trench isolation region with an excess amount of the silicon dioxide during selective deposition; and

planarizing the shallow trench isolation region by removing the excess amount.

13. (Currently Amended) The method according to claim 1, further comprising ~~the step of~~:

processing the selectively deposited silicon dioxide to ~~change its density to one~~ provide a density substantially similar to [[that]] a density of thermally grown silicon dioxide.

14. (Currently Amended) The method according to claim 13, wherein ~~the step of~~ processing the selectively deposited silicon dioxide further includes: ~~the step of~~

annealing the selectively deposited silicon dioxide at a temperature between approximately 800°C [[-]] and approximately 1200°C.

15-18. (Canceled)

19. (Withdrawn) A method of forming shallow trench isolation regions comprising the steps of:

forming a plurality of active regions on a silicon substrate;

forming a shallow trench isolation region between a first and a second active region from among the plurality of active regions; and

selectively depositing silicon dioxide in the shallow trench isolation region by liquid phase deposition of the silicon dioxide.

20. (Withdrawn-currently amended) The method according to claim 19, wherein ~~the step of~~ selectively depositing the silicon dioxide avoids depositing the silicon dioxide on the first and second active regions.

21. (Withdrawn-currently amended) The method according to claim 20, wherein the silicon substrate includes:

a silicon substrate;

a buried oxide layer on the silicon substrate; and

a silicon-on-insulator layer on the buried oxide layer and from which the active regions are formed.

22. (New) The method according to claim 6, further comprising:

forming a pad oxide layer between the pad nitride layer and the silicon-on-insulator layer.

23. (New) The method according to claim 22, wherein the pad oxide layer has a thickness between approximately 2 nm and approximately 10 nm.